

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max $T_c = +25^\circ C$
30V	5.5mΩ @ $V_{GS} = 10V$	45A
	9mΩ @ $V_{GS} = 4.5V$	30A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions
- DC-DC Converters
- Battery

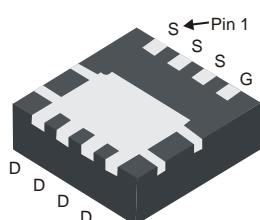
Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability

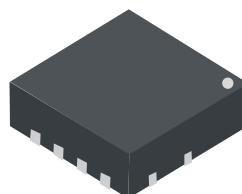
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)

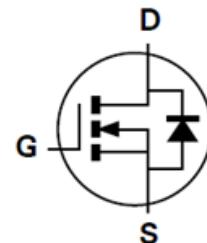
PowerDI3333-8



Bottom View



Top View



Equivalent Circuit

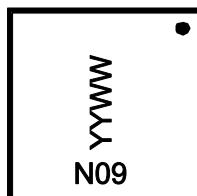
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3009SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMN3009SFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N09= Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 15 = 2015)
 WW = Week Code (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	I_D	16	A
		13	
	I_D	45	A
		35	
Pulsed Drain Current (380 μs Pulse, Duty Cycle = 1%)	I_{DM}	80	A
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	20	A
Avalanche Current, $L = 0.1\text{mH}$	I_{AS}	33	A
Avalanche Energy, $L = 0.1\text{mH}$	E_{AS}	55	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.9	W
		0.6	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	137	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	2.1	W
		1.4	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	7.8	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

 Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	5.5	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	—	9		$V_{GS} = 4.5\text{V}, I_D = 16\text{A}$
Diode Forward Voltage	V_{SD}	—	—	1	V	$V_{GS} = 0\text{V}, I_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	2,000	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	315	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	248	—	pF	
Gate Resistance	R_g	—	2.2	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	20	—	nC	$V_{DS} = 15\text{V}, I_D = 15\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	42	—	nC	
Gate-Source Charge	Q_{gs}	—	4.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	7.4	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.9	—	nS	$V_{DD} = 15\text{V}, V_{GS} = 10\text{V}, R_g = 3.3\Omega, I_D = 15\text{A}$
Turn-On Rise Time	t_R	—	4.1	—	nS	
Turn-Off Delay Time	$t_{D(OFF)}$	—	31	—	nS	
Turn-Off Fall Time	t_F	—	14.6	—	nS	
Reverse Recovery Time	t_{RR}	—	15	—	nS	$I_F = 15\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	6	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

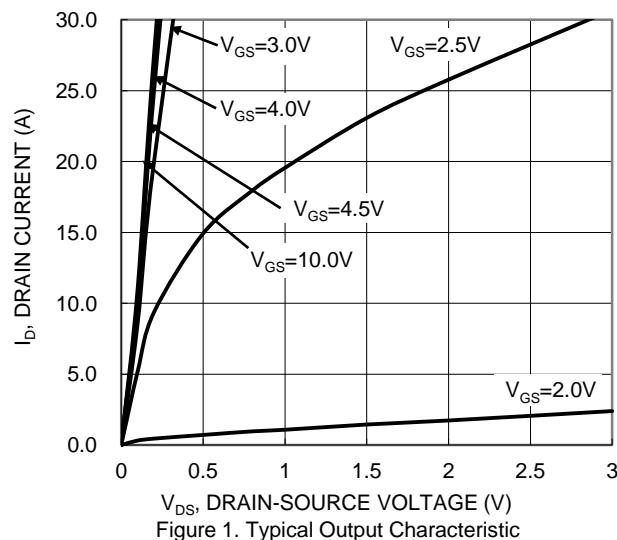


Figure 1. Typical Output Characteristic

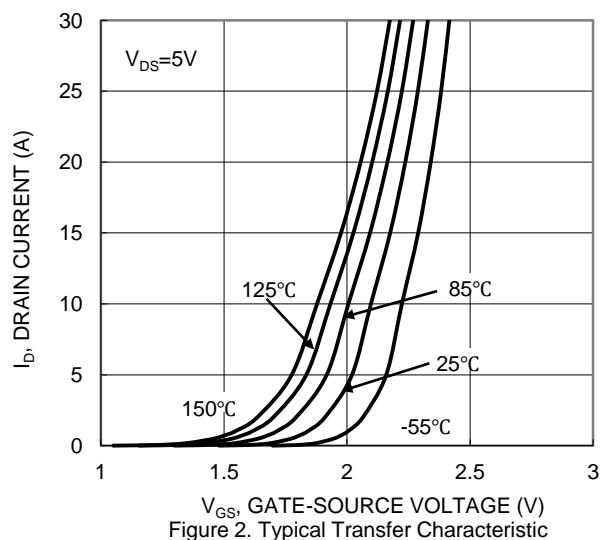


Figure 2. Typical Transfer Characteristic

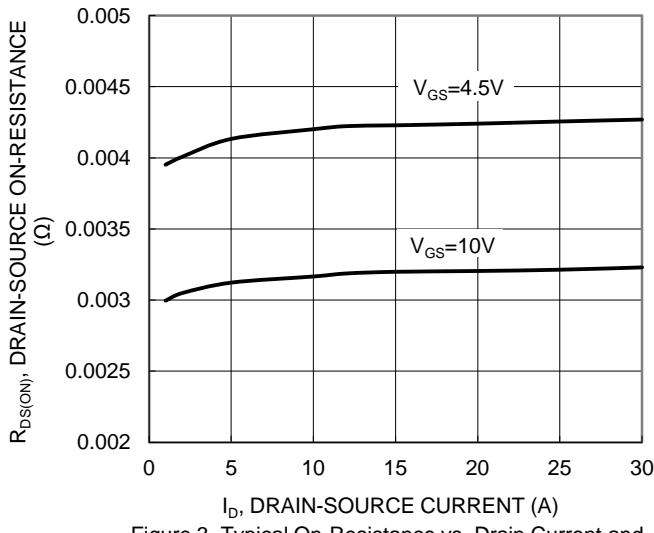


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

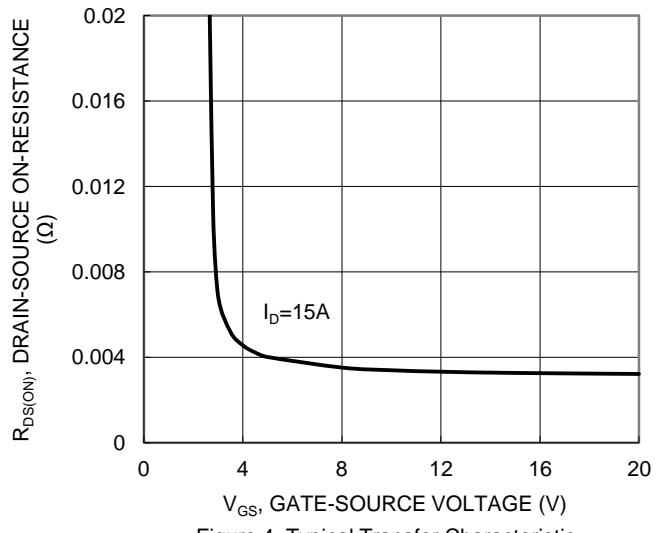


Figure 4. Typical Transfer Characteristic

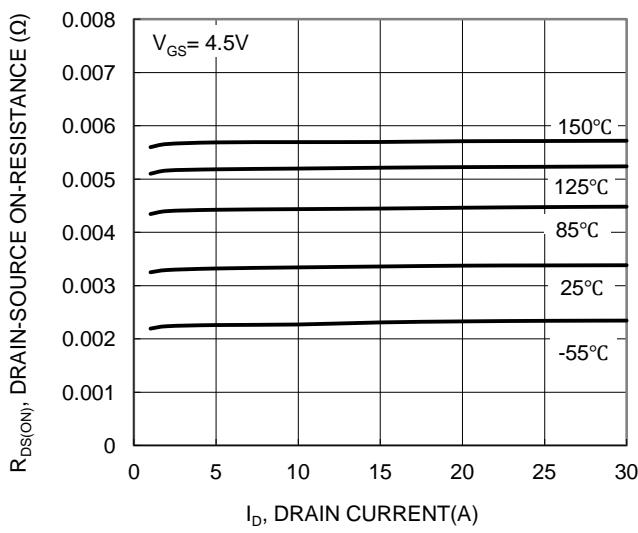


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

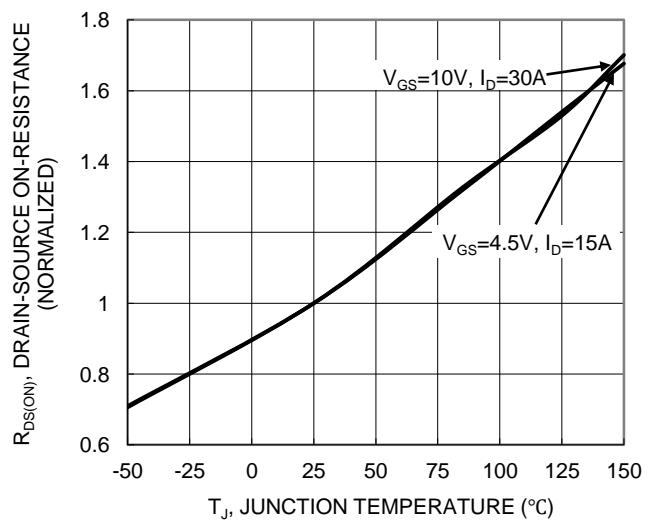
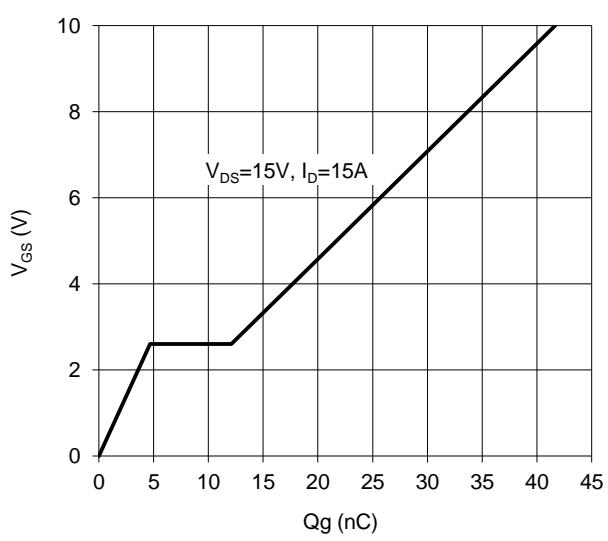
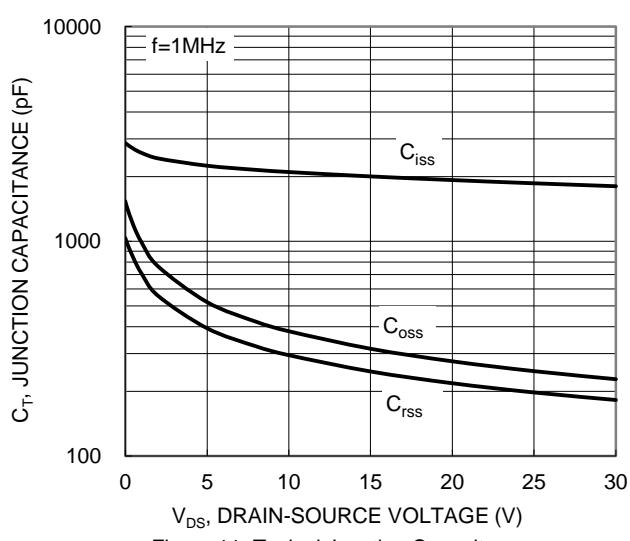
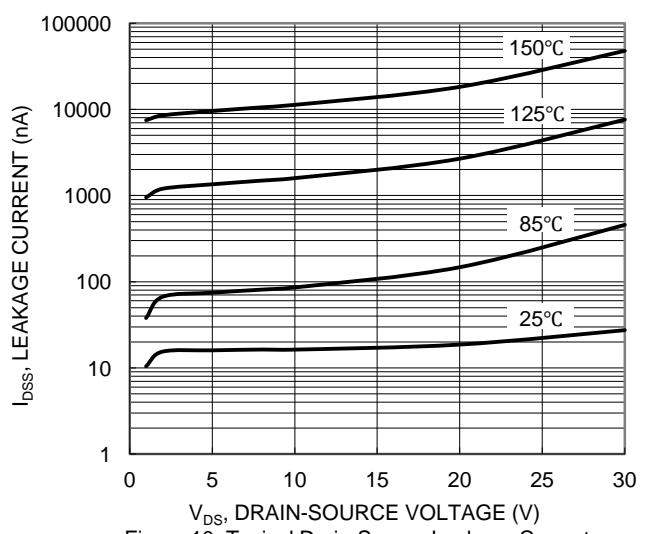
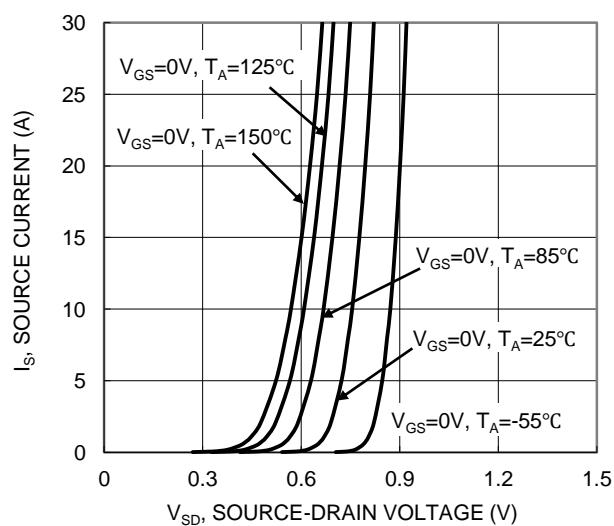
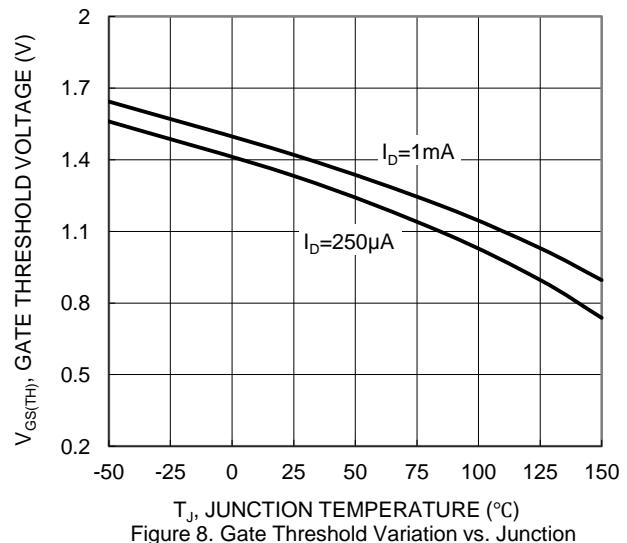
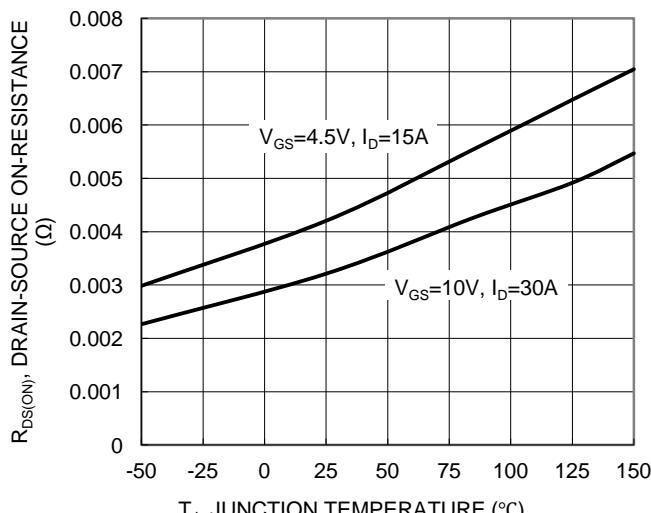


Figure 6. On-Resistance Variation with Temperature



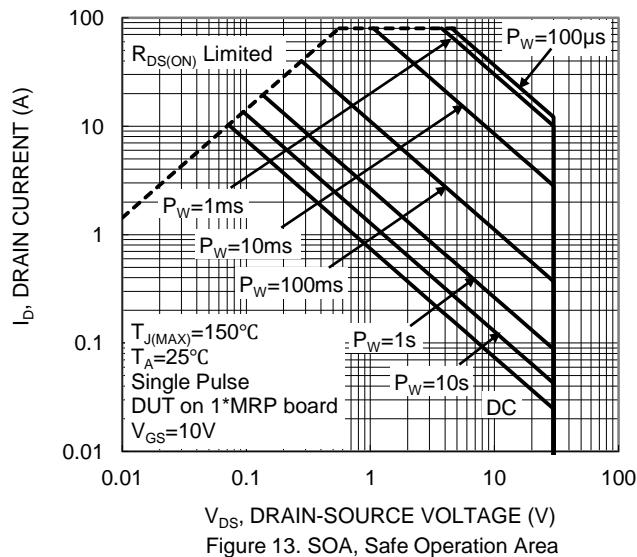


Figure 13. SOA, Safe Operation Area

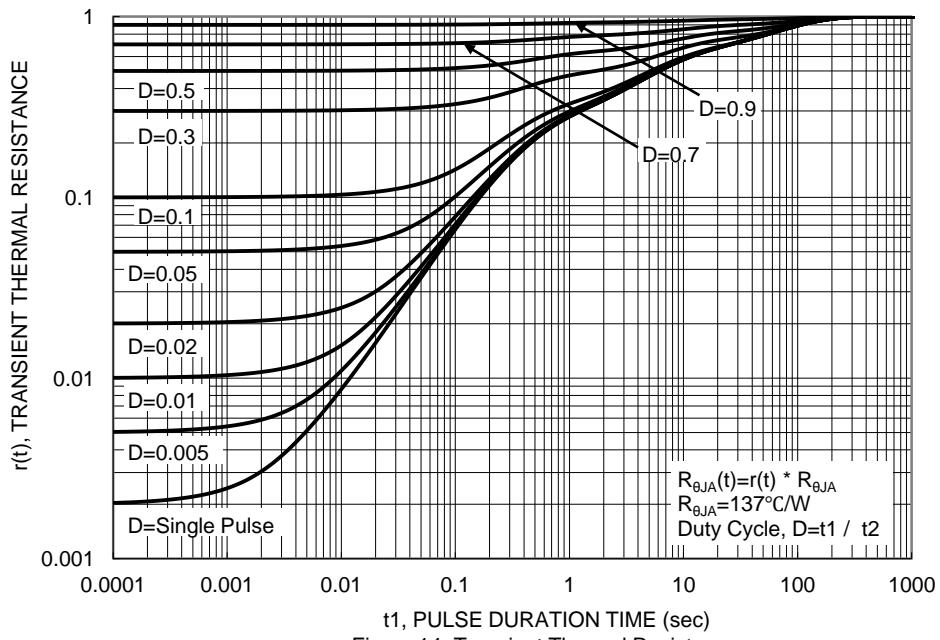
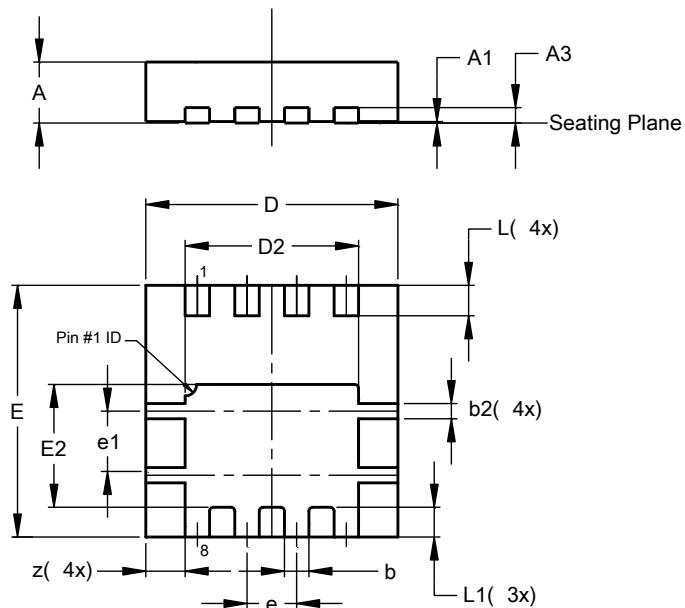


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

PowerDI3333-8



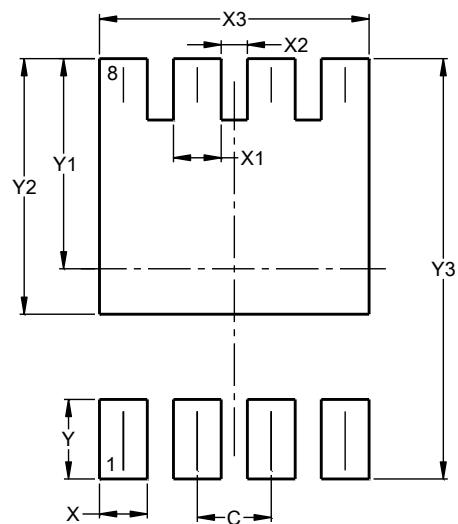
PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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